

PHASE CONTROL THYRISTORS

- **Junction Size:** Square 250 mils
- **Wafer Size:** 4"
- **V_{RRM} Class:** 600 to 1200 V
- **Passivation Process:** Glassivated MESA
- **Reference IR Packaged Part:** n. a.

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V _{TM} Maximum On-state Voltage	1.25 V	T _J = 25°C, I _T = 25 A
V _{DRM} /V _{RRM} Direct and Reverse Breakdown Voltage	600 to 1200 V	T _J = 25°C, I _{DRM} /I _{RRM} = 100 μA (1)
I _{GT} Max. Required DC Gate Current to Trigger	80 mA	T _J = 25°C, anode supply = 6 V, resistive load
V _{GT} Max. Required DC Gate Voltage to Trigger	2 V	T _J = 25°C, anode supply = 6 V, resistive load
I _H Holding Current Range	5 to 100 mA	Anode supply = 6 V, resistive load
I _L Maximum Latching Current	300 mA	Anode supply = 6 V, resistive load

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Chip Dimensions	250x250 mils (see drawing)
Wafer Diameter	100 mm, with std. <110> flat
Wafer Thickness	330 μm ± 10 μm
Maximum Width of Sawing Line	130 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR255SG..HCB

Preliminary Data Sheet I0211J 12/99

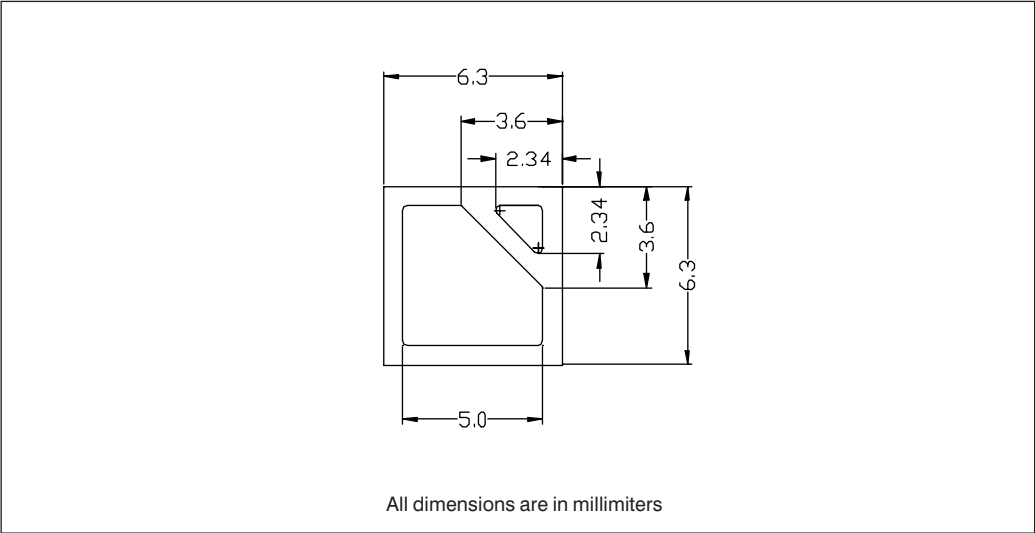
International
IR Rectifier

Ordering Information Table

Device Code						
IR	255	S	G	12	H	CB
1	2	3	4	5	6	7
1	- International Rectifier Device					
2	- Chip Dimension in Mils					
3	- Type of Device: S = Solderable SCR					
4	- Passivation Process: G = Glassivated MESA					
5	- Voltage code: Code x 100 = V_{RRM}					
6	- Metallization: H = Silver (Anode) - Silver (Cathode)					
7	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier					

Available Class
06 = 600 V
08 = 800 V
12 = 1200 V

Outline Table



Wafer Layout

